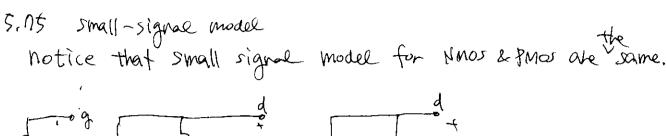
HW#8 Solution (Pub. sets) The property of the property 5,57 $q_{m} = \frac{\sqrt{J_0}}{\sqrt{V_{60}}} = \frac{2 \cdot J_0}{V_{60} - V_{70}}$ In this circuit, $V_p = V_q = 2V$ (: Iq=0 so no Voltage drop across Ra $\exists g_{m} = \frac{2.500 \, \text{M}}{2-0.9} = 9.09 \, \text{x} 10^{-9} \, (A/V)$ ro = VA = 100 KM, (roll RL) = 9,09 KM ·· 50 = -8,2645 If I increased to ImA, consider $I_0 = K \cdot (V_{qs} - V_t) \times (1 + \frac{V_{0s}}{V_n})$ For $I_0 = 500 \mu A$, $V_{gs} = 2$, we can find K. $: K = \frac{I_0}{(V_g - V_{t})^2 \cdot (1 + \frac{V_{ps}}{V_A})} = \frac{500 \mu A}{(2 - 0.9)^2 \cdot (1 + \frac{2}{50})} = 3.90 \times 10^4 (A/V_2)$ Hence, for Ip = (mA, new Vo = Vo is = IMA = K < Vo-Vt) 2 Cignored VA tam for simplicity) => / Vp = 2.48 with Vp = 2.48 & Zp = IMA, by following same way to find the gain, Av=-10,5057



$$\frac{d}{\sqrt{r_{in}}} = -\frac{d}{\sqrt{m_{i}}} \cdot r_{oi} \cdot \frac{d}{\sqrt{r_{in}}} = -\frac{d}{\sqrt{r_{in}}} =$$

1. Av =
$$\frac{s_0}{s_1}$$
 = (gm, r_{01}) (gm 2 r_{02})

Short-circuit transaconductoria
$$\frac{1}{\sqrt{2}}$$

Short-circuit transaconductoria $\frac{1}{\sqrt{2}}$

-) ishort =
$$-\frac{\sqrt{x}}{r_{02}} - gmz\sqrt{x} = -(gmzt\frac{1}{r_{02}})\sqrt{x} - 0$$

-) KCL at X: $gm\sqrt{x} + \frac{\sqrt{x}}{\sqrt{x}} + \frac{\sqrt{x}}{\sqrt{x}} + av\sqrt{x} = 0$

$$\Rightarrow \text{KCL at } X : g_{m_1} v_{\bar{n}} + \frac{v_{\kappa}}{v_{o_1}} + \frac{v_{\kappa}}{v_{o_2}} + g_{m_2} v_{\kappa} = 0$$

$$\Rightarrow v_{\kappa} = \frac{-g_{m_1} v_{\kappa}}{\left(\frac{1}{r_{o_1}} + \frac{1}{r_{o_2}} + g_{m_2}\right)}$$

Combining D&D gives

Nothert = (qm2+ 1/2) · (qm2+ 1/2) · (qm2+ 1/2)

= qm1Vi (· 1/20) · (integral)

= qm1Vi (· 1/20) · (integral)

current source is removed become vasi=0

$$\frac{1}{3} \frac{1}{5} \frac{1}{5} \frac{1}{5} = \frac{1}{5} \frac{$$

=> VT = IT (9m2 ro, roz + ro, troz)

-. Rout = gmz/o/Voz + Vol + Voz

Therefore, gain is boosted by the factor of gueron

2,8

Rig

$$(a) \qquad -\frac{100}{10} = -10$$

10KN

(oKs

10kp

loks

$$(e) \qquad O\left(-\frac{\circ}{10}\right)$$

loks

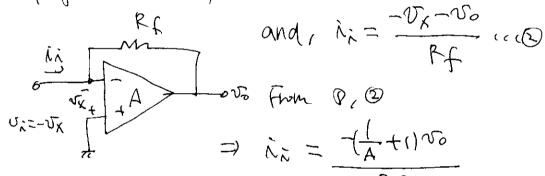
$$(f) \qquad -\infty \left(z - \frac{(ook)}{0} \right)$$

020

For
$$A=\infty$$
,
$$\nabla_{i}=0 \ (\because VCI=VCI) \ if \ A=\infty$$
Hence,

Hence,
$$\lambda_{i} = \frac{o - v_{0}}{R_{f}} \Rightarrow R_{m} = \frac{v_{0}}{\lambda_{i}} = -R_{f}$$

$$R_{in} = \frac{v_{i}}{P_{in}} = 0$$



and,
$$\lambda_{i} = \frac{-V_{k} - V_{o}}{P_{f}}$$

$$\tilde{N}_{\tilde{n}} = \frac{\left(\frac{1}{A} + 1\right) \tilde{N}_{0}}{Pf}$$

Pm =
$$\frac{v_0}{aa} = -\frac{Rf}{1+\frac{1}{A}}$$

$$Piq = \frac{v\lambda}{\lambda i}$$
, $\lambda_i = \frac{-v_X - A \cdot v_X}{Pf} = \frac{C(tA)}{Pf} \cdot v_A$

$$I_{b} = \frac{1}{2} \int_{0}^{M} C_{dX} \frac{W}{L} \left(V_{ih} - V_{b} \right)$$
 (2)

at the eage of patenation, Vout = Vin-Ve

$$V_{in} - V_{t} = 3 - 10K I_{D} = 3 - 10 \cdot \frac{1}{2} \frac{H}{n} \cos \frac{M}{L} (V_{in} - V_{t})$$

$$Cox = \frac{60x}{60x} = \frac{3.9 \times 8.85 \times 10^{-12} F/m}{10^{-7} m} = 345.2 \times 10^{-16} f/m^{-1}$$

$$I_{in}^{\mu} = 600 \frac{Cm^{\frac{1}{2}}}{5.7} (F_{non} \text{ Spice model})$$

$$\Rightarrow I_{in}^{\mu} Cox = 600 \times 10^{-4} \times 345.2 \times 10^{-6} = 20.7 \times 10^{-6} f/m^{-1}$$

$$V_{in} - V_{t} = 3 - 10 \times \frac{1}{2} \times 20.7 \times 10 \times 10 (V_{in} - V_{t})^{-1}$$

$$\Rightarrow V_{in} - V_{t} = 1.29 \qquad ; V_{t} = 0.7 (f_{non} \text{ SPICE model})$$

$$\Rightarrow V_{in} = 1.99 V$$

There is very close to the simulated value.

In Simulation, the intersection of Vout & Vin - Ve occurs at Vin = 1.992

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*Common-Source MOS Amplifier Circuit
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** Circuit Description **

* Power Supplies Vdd Vdd 0 DC 3V Vss Vss 0 DC 0V

- * Input Voltage Vin in 0 DC 0V AC 1V
- * Common-Source Circuit * MOS D G S B MO out in Vss Vss nch L=0.5u W=5u Rd Vdd out 10k
- * Model Definitions
- * TOX = Oxide thickness in Meters * U0 = Surface mobility in cm/Vs
- * VTO = Zero-bias threshold voltage in V
- * LAMBDA = channel-length modulation in 1/V
- * CBD = base-drain junction capacitance
- * CBS = base-source junction capacitance
- .model nch nmos (LEVEL=1 TOX=1e-7 U0=600 +VTO=0.7 LAMBDA=0.02 CBD=20fF +CBS=20fF)
- ** Analysis Request **
- * DC Analysis (SOURCE START STOP INCREMENT)
 .dc Vin 0V 3V 5mV
- ** Output Request **
- .probe

.end

